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## INTERNATIONAL RELIABILITY PHYSICS SYMPOSIUM AWARD PRESENTATION



Dave Barber (*center*) received the award from General Chairman George Ebel (*left*), and Board Member Al Tamburrino (*right*).

The International Reliability Physics Symposium Award for Outstanding Contributions in the Field of Reliability Physics was first authorized in 1971 by the Symposium Board of Directors. This award, which is not necessarily given annually, is presented to individuals who have made major significant contributions to the advancement of the field of reliability.

The 1984 award is presented to DAVID F. BARBER in recognition of his numerous contributions to the field of Reliability Physics. Mr. Barber, Chief of the Reliability Branch at RADC for over seventeen years before his retirement in 1979, was an innovator in applying materials science, device design and process engineering, and electronics to what had been a primarily statistical discipline. He brought "physics of failure" out of the laboratory closet for direct support to the systems projects and fielded equipment. He was the energetic and effective executive who provided scientific personnel from the reliability physics laboratories to support the Component Quality Assurance Program for the Minuteman II, one of the first applications of integrated circuits in military hardware. Mr. Barber was

also one of the first in government to recognize the revolutionary impact of microprocessor devices for military electronics, and, in 1977, organized a team of engineers and reliability scientists to encourage the application, standardization, and reliability qualification of these devices. Mr. Barber has also given years of dedicated service to this symposium as a member of the Management Committee, as a member of the Board of Directors, and as General Chairman of the Symposium. A Senior Member of the IEEE, he served on the ADCOM of the Reliability Society. He has also been closely associated with the Annual Reliability and Maintainability Symposium, the Government Microelectronic Applications Conference (GOMAC) and the EOS/ESD Symposium. Mr. Barber has been a man of breadth as well as depth, being well known for his work in the Association of School Boards at the State level in New York, public spirited organizations such as Rotary, and is an avid sportsman—and a sportscaster for the Women's PGA. He is presently the President of Scien-Tech Associates, a Conference Management Consultant firm, which is engaged by IRPS for publications and arrangements.

# TABLE OF CONTENTS

## METALLIZATION

Session Chairman: Robert K. Lowry

Reliability Implications of Nitrogen Contamination During Deposition of Sputtered Aluminum/Silicon Metal Films <i>J. Klema, R. Pyle and E. Domangue</i> .....	1
New Failure Mechanisms in Sputtered Aluminum-Silicon Films <i>J. Curry, G. Fitzgibbon, Y. Guan, R. Muollo, G. Nelson and A. Thomas</i> .....	6
Silicon Inclusions in Aluminum Interconnects <i>S. J. O'Donnell, J. W. Bartling and G. Hill</i> .....	9
The Physics and Reliability of Fusing Polysilicon <i>A. Ito, E. W. George, R. K. Lowry and H. A. Swasey</i> .....	17
Reliability of High Temperature I <sup>2</sup> L Integrated Circuits <i>D. C. Dening, D. J. LaCombe and A. Christou</i> .....	30
Epoxy Degradation Induced Au-Al Intermetallic Void Formation in Plastic Encapsulated MOS Memories <i>R. J. Gale</i> .....	37
The Relationship Between Electromigration-Induced Short-Circuit and Open-Circuit Failure Times in Multi-Layer VLSI Technologies <i>J. R. Lloyd and J. A. Knight</i> .....	48

## GaAs DEVICE RELIABILITY

Session Chairman: Walter Slusark, Jr.

Theoretical and Experimental Studies of Failure Mechanisms in Gallium Arsenide Three-Terminal Transferred Electron Devices <i>H. L. Grubin, W. T. Anderson and A. Christou</i> .....	52
Reliability of Gate Metallization in Power GaAs MESFETs <i>K. Katsukawa, Y. Kose, M. Kanamori and S. Sando</i> .....	59

## FAILURE ANALYSIS—LASER TECHNIQUES

Session Chairman: Daniel J. Burns

Latch-up Analysis on a 64K-Bit Full CMOS Static RAM Using a Laser Scanner <i>T. Shiragasawa, H. Shimura, K. Kagawa, T. Yonezawa and M. Noyori</i> .....	63
Logic Failure Analysis of CMOS VLSI Using a Laser Probe <i>F. J. Henley</i> .....	69
Reliability/Design Assessment by Internal-Node Timing—Margin Analysis Using Laser Photocurrent-Injection <i>D. J. Burns, M. T. Pronobis, C. A. Eldering and R. J. Hillman</i> .....	76

# MICROANALYTICAL TECHNIQUES

Session Chairman: Thomas J. Rossiter

Novel Sample Preparations for Microanalysis <i>R. W. Belcher, G. P. Hart and W. R. Wade</i> .....	83
Dynamic Fault Imaging of VLSI Random Logic Devices <i>T. C. May, G. L. Scott, E. S. Meieran, P. Winer and V. R. Rao</i> .....	95
Semiconductor Junction Temperature Measurement Using the Electron Beam Induced Current Mode in the Scanning Electron Microscope <i>J. M. Patterson</i> .....	109

## FAILURE PREDICTION AND DETECTION

Session Chairman: Thomas J. Every

Predicting Oxide Failure Rates Using the Matrix of a 64K DRAM Chip <i>D. Wendell, D. Segers and B. Wang</i> .....	113
Improved Sensitivity for Hot Spot Detection Using Liquid Crystals <i>D. Burgess and P. Tan</i> .....	119
Pulsed Infra-Red Microscopy for Debugging Latch-up on CMOS Products <i>N. Khurana</i> .....	122
Lifetime of Bonded Contacts on Thin Film Metallizations <i>H. Hieber and K. Pape</i> .....	128
Effect of Silicon Inclusions on the Reliability of Sputtered Aluminum- Silicon Metallization <i>S. B. Herschbein, P. A. Zulpa and J. M. Curry</i> .....	134

## OXIDE BREAKDOWN

Session Chairman: Walter H. Schroen

Determination of Reliability from Ramped Voltage Breakdown Experiments; Application to Dual Dielectric MIM Capacitors <i>M. Shatzkes, M. Av-Ron and K. V. Srikrishnan</i> .....	138
Reliability Prediction Using Large MOS Capacitors <i>E. Domangue, R. Rivera and C. Shepard</i> .....	140
Time Dependent Dielectric Breakdown Measurement of High Pressure Low Temperature Oxidized Film <i>M. Hirayama, T. Matsukawa, N. Tsubouchi and H. Nakata</i> .....	146
Characteristics and Reliability of 100 Å Oxides <i>D. A. Baglee</i> .....	152
Impact of Advances in Technology on the Properties of Si/SiO <sub>2</sub> Interface <i>A. G. Sabnis</i> .....	156
An Ion Implant Induced Instability Mechanism in CMOS/SOS Device <i>E. B. Spialter, J. V. Brandewie and R. A. Kjar</i> .....	161

Snapback Induced Gate Dielectric Breakdown in Graded Junction MOS Structures <i>S. N. Shabde, G. Simmons, A. Baluni and D. Back.</i> .....	165
--	-----

## DIE ATTACH

**Session Chairman: Ajit Goel**

AES/ESCA/SEM/EDX Studies of Die Bond Materials and Interfaces <i>T. P. L. Li, E. L. Zigler and D. E. Hillyer</i> .....	169
Characterization of Die Attach Failure Modes in Leadless Chip Carrier (LCC) Packages by Auger Electron Spectroscopy <i>R. E. Pyle and H. A. Stevens</i> .....	175
Initial Wetting and Reaction Sequences in Soldering <i>G. A. Walker and P. W. DeHaven</i> .....	181

## CONTACT AND INTERCONNECT RELIABILITY

**Session Chairperson: Sheila Vaidya**

TaSi <sub>x</sub> as a Barrier Between Al-Based Metallization and n <sup>+</sup> - and p <sup>+</sup> - Si for Reliable VLSI Contacts <i>F. Neppl, F. Fischer and U. Schwabe</i> .....	185
Sputtered Ti-Doped Al-Si for Enhanced Interconnect Reliability <i>F. Fischer and F. Neppl</i> .....	190
Mechanism of Oxide Leakage Current of Silicide Gate MOSFETs <i>T. Watanabe, H. Ishiuchi, T. Tanaka, T. Mochizuki and O. Ozawa</i> .....	193

## FET RELIABILITY

**Session Chairman: David S. Yaney**

The Effect of TaSi <sub>2</sub> /n <sup>+</sup> Poly Gate on Hot-Electron Instability of Small Channel MOSFETs <i>L. Manchanda</i> .....	199
Reduction of V <sub>T</sub> Shift Due to Avalanche Hot Carrier Injection Using Graded Drain Structures in Submicron N-Channel MOSFETs <i>M. Noyori, Y. Nakata, S. Odanaka and J. Yasui</i> .....	205
Turn-on Voltage Degradation of Short Channel MOSFETs Due to Generation of Interface States <i>I. Eisele, P. Vitanov, F. Fischer and U. Schwabe</i> .....	210

## PASSIVATION

**Session Chairman: Robert B. Merrett**

Polyimide Adhesion Characteristics <i>R. G. Narechania, J. A. Bruce and C. A. Beach</i> .....	214
Moisture Resistive, U. V. Transmissive Passivation for Plastic Encapsulated EPROM Devices <i>K. Alexander, J. Hicks and T. Soukup</i> .....	218

Phosphorus Migration Kinetics from PSG to Glass Passivation Surface <i>G. DiGiacomo</i> .....	223
--	-----

Polyimide Interlevel Insulation Process/Design Limitations <i>D. L. Bergeron, J. P. Kent and K. E. Morrett</i> .....	229
---	-----

## INTERCONNECT ELECTROMIGRATION

**Session Chairman: Michael J. McNutt**

The Role of Thermal Grooving, Thermotransport and Electrotransport on the Failure of Thin Film Metallizations <i>R. E. Hummel, S. M. Goho and R. T. DeHoff</i> .....	234
---	-----

Electromigration Induced Damage and Structure Change in Cr-Al/Cu and Al/Cu Interconnection Lines <i>E. Levine and J. Kitcher</i> .....	242
---	-----

Effect of Passivation and Passivation Defects on Electromigration Failure in Aluminum Metallization <i>H. A. Schafft, C. D. Younkins, T. C. Grant, C.-Y. Kao and A. N. Saxena</i> .....	250
--	-----

Acoustic Emission Study of Electromigration Damage in Al-Cu Thin Film Conductor Stripes <i>E. T. Severn, H. H. Huston and J. R. Lloyd</i> .....	256
--	-----

Comparative Electromigration Tests of Al-Cu Alloys <i>P. Merchant and T. Cass</i> .....	259
--	-----

Electromigration Evaluation—MTF Modeling and Accelerated Testing <i>T. A. Burkett and R. L. Miller</i> .....	264
---	-----

Electromigration Study of the Al-Cu/Ti/Al-Cu System <i>S. Iyer and C.-Y. Ting</i> .....	273
--	-----

## FULL COLOR PHOTO SECTION

Technical Paper Color Figures and Symposium Chairmen .....	279
--	-----